

CBAT754
CBAT754A
CBAT754C
CBAT754S

SURFACE MOUNT
SILICON SCHOTTKY DIODES



CBAT754: SINGLE
CBAT754A: DUAL, COMMON ANODE
CBAT754C: DUAL, COMMON CATHODE
CBAT754S: DUAL, IN SERIES

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	30	V
Continuous Forward Current	I_F	200	mA
Peak Repetitive Forward Current	I_{FRM}	300	mA
Forward Surge Current, $t_p=10\text{ms}$	I_{FSM}	600	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MAX	UNITS
I_R	$V_R=25\text{V}$	2.0	μA
V_F	$I_F=0.1\text{mA}$	200	mV
V_F	$I_F=1.0\text{mA}$	260	mV
V_F	$I_F=10\text{mA}$	340	mV
V_F	$I_F=30\text{mA}$	420	mV
V_F	$I_F=100\text{mA}$	500	mV
C_d	$V_R=1.0\text{V}, f=1.0 \text{ MHz}$	10	pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$	5.0	ns

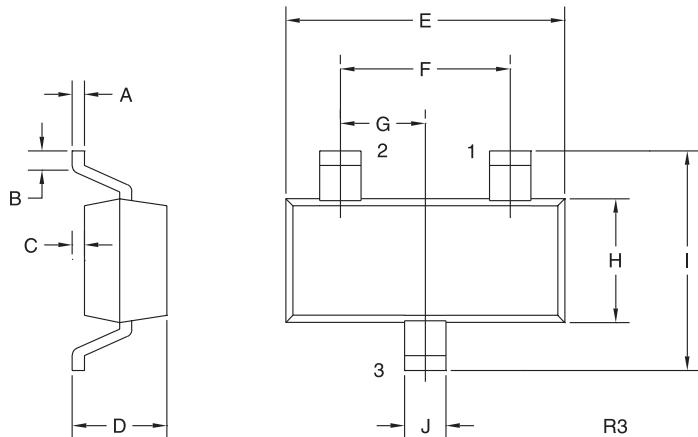
CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBAT754 Series types are Silicon Schottky Diodes in an SOT-23 Surface Mount Package.

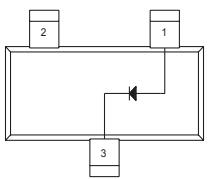
SURFACE MOUNT
SILICON SCHOTTKY DIODES

SOT-23 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075	-	1.90	-
G	0.037	-	0.95	-
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

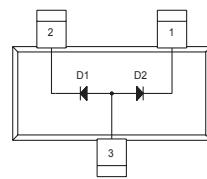
SOT-23 (REV: R3)



LEAD CODE:

CBAT754
1) Anode
2) No Connection
3) Cathode

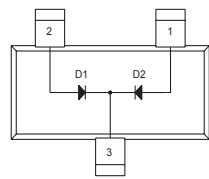
**MARKING
CODE: C2K**



LEAD CODE:

CBAT754A
1) Cathode D2
2) Cathode D1
3) Anode D1, Anode D2

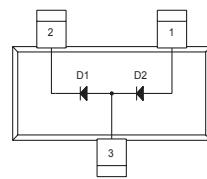
**MARKING
CODE: C2LA**



LEAD CODE:

CBAT754C
1) Anode D2
2) Anode D1
3) Cathode D1, Cathode D2

**MARKING
CODE: C2MC**



LEAD CODE:

CBAT754S
1) Anode D2
2) Cathode D1
3) Anode D1, Cathode D2

**MARKING
CODE: C2NS**